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TECHNOLOGY CENTER

APPLICATION NO. GIANNUZZI 3-19-12

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

(1) Kindly rewrite Claim 25 as follows:

25. (Amended) An interconnect structure, comprising:

a nucleation layer including a first metal located over a barrier layer within an opening in
a dielectric layer, wherein the nucleation layer includes substantially uniform grains;
an intermediate layer including a second metal located over the nucleation layer; and
a bulk plug layer including the first metal located over the intermediate layer.